

# MOS FIELD EFFECT TRANSISTOR $\mu$ PA2708GR

## SWITCHING N-CHANNEL POWER MOS FET

#### **DESCRIPTION**

The  $\mu$ PA2708GR is N-channel MOS Field Effect Transistor designed for DC/DC converter and power management applications of notebook computer.

#### **FEATURES**

• Low on-state resistance

 $R_{DS(on)1} = 5.5 \text{ m}\Omega \text{ MAX.}$  (VGS = 10 V, ID = 9.0 A)  $R_{DS(on)2} = 7.5 \text{ m}\Omega \text{ MAX.}$  (VGS = 4.5 V, ID = 9.0 A)

- Low Ciss: Ciss = 4700 pF TYP. (VDS = 10 V, VGS = 0 V)
- Small and surface mount package (Power SOP8)

#### ORDERING INFORMATION

PART NUMBER	PACKAGE
μPA2708GR-E1	Power SOP8
μPA2708GR-E2	Power SOP8
μPA2708GR-E1-A Note	Power SOP8
μ PA2708GR-E2-A Note	Power SOP8

**Note** Pb-free (This product does not contain Pb in external electrode and other parts.)

#### ABSOLUTE MAXIMUM RATINGS (TA = 25°C, All terminals are connected.)

Drain to Source Voltage (V <sub>GS</sub> = 0 V)	VDSS	30	V
Gate to Source Voltage (VDS = 0 V)	Vgss	±20	V
Drain Current (DC)	ID(DC)	±17	Α
Drain Current (pulse) Note1	ID(pulse)	±68	Α
Total Power Dissipation Note2	P <sub>T1</sub>	1.1	W
Total Power Dissipation (PW =10 sec) Note2	P <sub>T2</sub>	2.5	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C
Single Avalanche Current Note3	las	17	Α
Single Avalanche Energy Note3	Eas	28.9	mJ

**Notes 1.** PW  $\leq$  10  $\mu$ s, Duty Cycle  $\leq$  1%

- 2. Mounted on glass epoxy board of 1 inch x 1 inch x 0.8 mm
- 3. Starting T<sub>ch</sub> = 25°C, V<sub>DD</sub> = 15 V, R<sub>G</sub> = 25  $\Omega$ , L = 100  $\mu$ H, V<sub>GS</sub> = 20  $\rightarrow$  0 V

#### THERMAL RESISTANCE

Channel to Ambient Note	Rth(ch-A)	114	°C/W
Channel to Drain Lead Note	Rth(ch-L)	30	°C/W

Note Mounted on glass epoxy board of 1 inch x 1 inch x 0.8 mm

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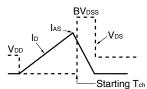
#### **ELECTRICAL CHARACTERISTICS (TA = 25°C, All terminals are connected.)**

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V			10	μΑ
Gate Leakage Current	Igss	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA
Gate Cut-off Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	1.0		2.5	٧
Forward Transfer Admittance Note	y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 9.0 A	10			S
Drain to Source On-state Resistance Note	RDS(on)1	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 9.0 A		4.5	5.5	mΩ
	RDS(on)2	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 9.0 A		5.6	7.5	mΩ
Input Capacitance	Ciss	V <sub>DS</sub> = 10 V		4700		pF
Output Capacitance	Coss	V <sub>GS</sub> = 0 V		670		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		340		pF
Turn-on Delay Time	<b>t</b> d(on)	V <sub>DD</sub> = 15 V, I <sub>D</sub> = 9.0 A		19		ns
Rise Time	<b>t</b> r	V <sub>GS</sub> = 10 V		26		ns
Turn-off Delay Time	<b>t</b> d(off)	R <sub>G</sub> = 10 Ω		100		ns
Fall Time	t <sub>f</sub>			27		ns
Total Gate Charge	<b>Q</b> G	V <sub>DD</sub> = 15 V		38		nC
Gate to Source Charge	Qgs	V <sub>GS</sub> = 5 V		13		nC
Gate to Drain Charge	Q <sub>GD</sub>	I <sub>D</sub> = 17 A		12		nC
Body Diode Forward Voltage Note	V <sub>F(S-D)</sub>	I <sub>F</sub> = 17 A, V <sub>GS</sub> = 0 V		0.8		٧
Reverse Recovery Time	trr	I <sub>F</sub> = 17 A, V <sub>GS</sub> = 0 V		33		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/μs		27		nC
Gate Resistance	Rg	f = 1 MHz		1.2		Ω

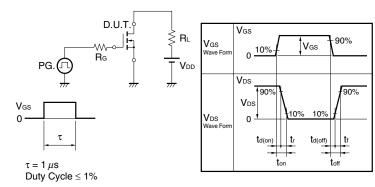
Note Pulsed

#### **TEST CIRCUIT 1 AVALANCHE CAPABILITY**

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#### TEST CIRCUIT 2 SWITCHING TIME

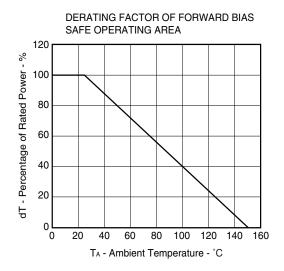


#### **TEST CIRCUIT 3 GATE CHARGE**

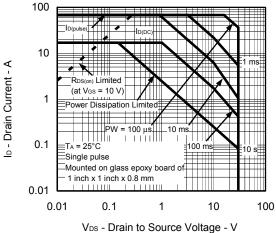
$$\begin{array}{c|c} D.U.T. \\ \hline I_G = 2 \text{ mA} \\ \hline \end{array}$$

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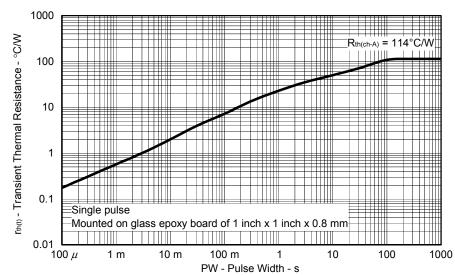
#### TYPICAL CHARACTERISTICS (TA = 25°C)



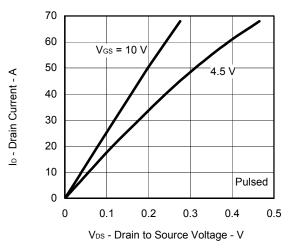
### FORWARD BIAS SAFE OPERATING AREA



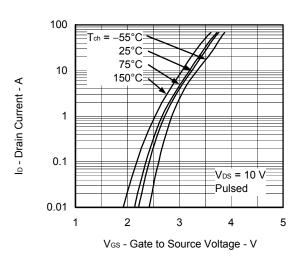
#### TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



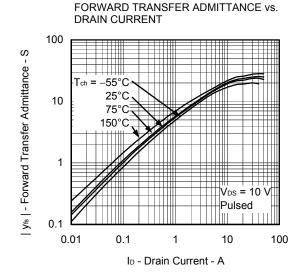
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE

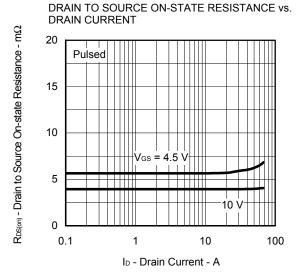


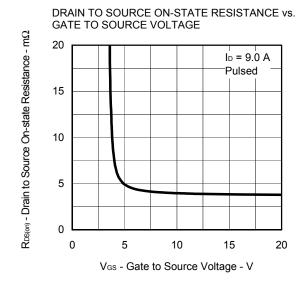
#### FORWARD TRANSFER CHARACTERISTICS

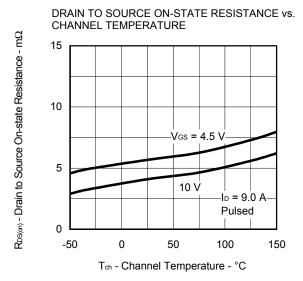


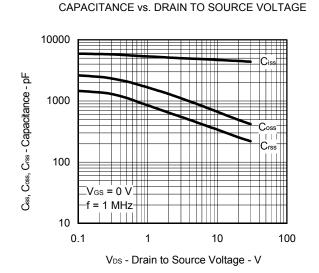
#### GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE 3 2.5 VGS(off) - Gate Cut-off Voltage - V 2 1.5 1 V<sub>DS</sub> = 10 V 0.5 Pulsed 0 -50 0 50 100 150 Tch - Channel Temperature - °C









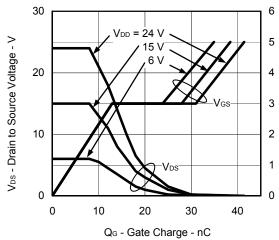


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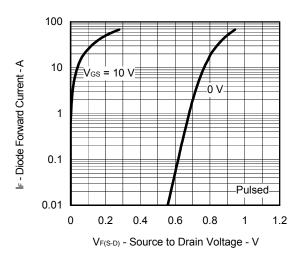
Ves - Gate to Source Voltage - V

#### **SWITCHING CHARACTERISTICS** 1000 ta(on), tr, ta(off), tr - Switching Time - ns td(off) 100 10 V<sub>DD</sub> = 15 V V<sub>GS</sub> = 10 V $R_G = 10 \Omega$ 0.1 1 10 100 ID - Drain Current - A

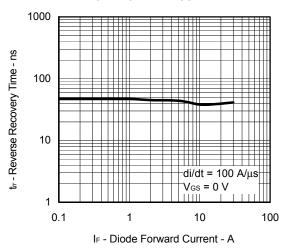
#### DYNAMIC INPUT/OUTPUT CHARACTERISTICS



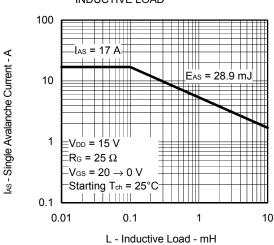
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



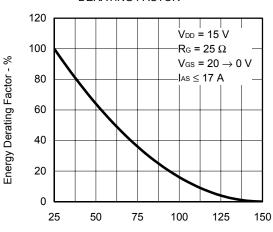
REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT



SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD



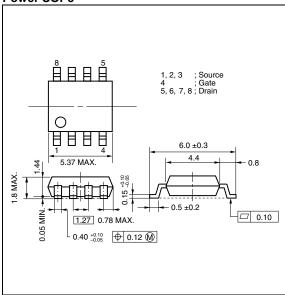
SINGLE AVALANCHE ENERGY **DERATING FACTOR** 



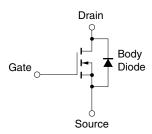
Starting Tch - Starting Channel Temperature - °C

#### PACKAGE DRAWING (Unit: mm)

#### Power SOP8



#### **EQUIVALENT CIRCUIT**



**Remark** Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

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